



SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

PRELIMINARY

**SSR2040M
SSR2040Z**

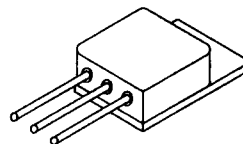
Designer's Data Sheet

FEATURES:

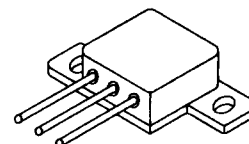
- Extremely Low Forward Voltage Drop
 - Hermetically Sealed Isolated Power Package
 - Guard ring for overvoltage protection
 - Eutectic Die Attach
 - 150°C Operating Junction Temperature
 - Ceramic seals for lead forming
-
- TX, TXV, and Space Level Screening Available

**20 AMP
40 VOLTS
SCHOTTKY
RECTIFIER**

TO-254



TO-254Z



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage	VRRM	40	Volts
	VRWM		
	VR		
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	IO	20	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on IO, allow junction to reach equilibrium between pulses, TA=25°C)	IFSM	300	Amps
Operating and storage temperature	Top & Tstg	-65 to +150	°C
Maximum Thermal Resistance Junction to Case	RθJC	1.5	°C/W

Available with Glass or Ceramic Seals. Contact Factory for Details.

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET#: RS0159 B

MED

SSR2040M SSR2040Z

PRELIMINARY



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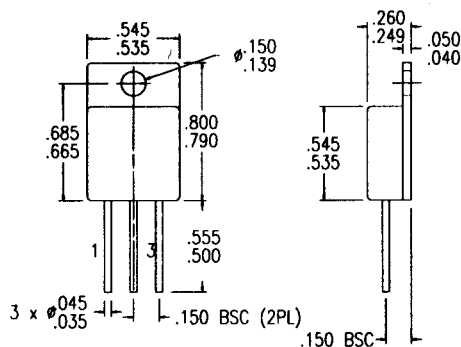
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ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop ($I_F = 5 \text{ A dc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 10 \text{ A dc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 20 \text{ A dc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse)	VF1	0.40 0.50 0.68	Vdc
Instantaneous Forward Voltage Drop ($I_F = 10 \text{ A dc}$, $T_A = -55^\circ\text{C}$, 300 μs Pulse)	VF2	0.55	Vdc
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ\text{C}$, 300 μs pulse minimum)	IR1	5	mA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ\text{C}$, 300 μs pulse minimum)	IR2	200	mA
Junction Capacitance ($V_R = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$)	CJ	800	pf

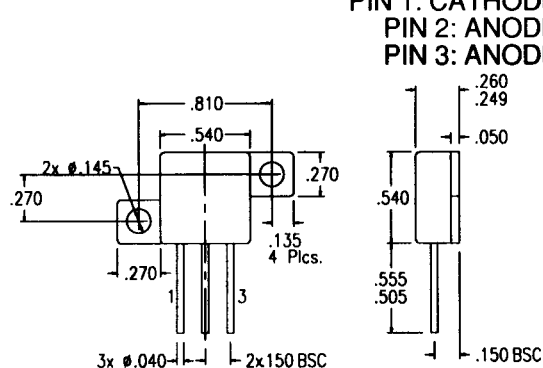
CASE OUTLINE: TO-254

PIN OUT:
PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



CASE OUTLINE: TO-254Z

PIN OUT:
PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



TYPICAL OPERATING CURVES

($T_A = 25^\circ\text{C}$ Unless otherwise specified)

